### FTSC

High temp. wire-bondable Si Capacitors up to 200°C



#### **Key features**

- Ultra High operating temperature up to 200°C
- Low profile (250 μm)
- High stability (temperature, voltage and aging)
- Low leakage current
- High reliability
- Dedicated to high temperature wire-bonding

(please refer to our Assembly Application Note for more details)

# **Key applications**

- All applications up to 200°C, such as aerospace, downhole and automotive industries
- High reliability applications
- Replacement of X7R and C0G dielectrics
- Decoupling / Filtering / Charge pump (i.e.: motor management, temperature sensors)
- Downsizing

Thanks to the unique Murata\* Silicon capacitor technology, most of the problems encountered in demanding applications can be solved. The High Temperature Wirebond Silicon Capacitors are dedicated to applications where reliability up to 200°C is the main parameter. ETSC are the most appropriate solution for Chip On Board, Chip On Foil, Chip On Glass, Chip On Ceramic, flip chip and embedded applications. This technology features a capacitor integration capability (up to 250 nF/mm<sup>2</sup>) which offers capacitance value similar to X7R dielectric, but with better electrical performances than COG/NPO dielectrics, up to 200°C.

ETSC provides the highest capacitor stability over the full -55°C/+200°C temperature range in the market with a temperature coefficient equals to+60 ppm/K. The Murata Silicon technology offers industry leading performances relative to failure rate with a FIT<0.017 parts/billions hours. This technology also offers high reliability, up to 10 times better than alternative capacitor technologies, such as Tantalum or MLCC, and eliminates cracking phenomena. This Silicon based technology is ROHS compliant.



<sup>\*</sup>Murata Integrated Passive Solutions



## **Electrical specifications**

| ETSC.xxx         | High Temp. Wirebondable Si Capacitors<br>from -55°C to 200°C |      |           |           |  |  |
|------------------|--|------|-----------|-----------|--|--|
| Part number      | Capacitance  | BV   | Case size | Thickness |  |  |
| 935124730510-xxA | 10 nF  | 30 V | 0202      | 250 µm    |  |  |
| 935124421610-xxA | 100 nF   | 11 V | 0404      | 250 µm    |  |  |
| 935124733610-xxA | 100 nF   | 30 V | 0605      | 250 μm    |  |  |
| 935124422622-xxA | 220 nF   | 11 V | 0505      | 250 μm    |  |  |
| 935124424710-xxA | 1 µF   | 11 V | 1208      | 250 μm    |  |  |
| 935124736710-xxA | 1 µF   | 30 V | 1616      | 250 μm    |  |  |
| 935124425722-xxA | 2.2 µF   | 11 V | 1612      | 250 μm    |  |  |
| 935124426733-xxA | 3.3 µF   | 11 V | 1616      | 250 µm    |  |  |
| 935124427747-xxA | 4.7 µF   | 11 V | 2016      | 250 μm    |  |  |

| Parameter                                    | Value                                    |  |  |  |  |
|--|--|--|--|--|--|
| Capacitance range                            | 390 pF to 4.7 μF                         |  |  |  |  |
| Capacitance tolerance                        | ±15 %(*)                                 |  |  |  |  |
| Operating temperature range                  | -55°C to 200°C                           |  |  |  |  |
| Storage temperature                          | -70°C to 215°C(**)                       |  |  |  |  |
| Temperature coefficient                      | +60 ppm/K                                |  |  |  |  |
| Breakdown voltage (BV)                       | 11 VDC or 30 VDC                         |  |  |  |  |
| Capacitance variation versus RVDC            | 0.1 %/V (from 0 to RVDC)                 |  |  |  |  |
| Insulation resistance                        | 100 GΩ @ 3 V, @ 25°C, t>120s, for 100 nF |  |  |  |  |
| Aging  | Negligible, < 0.001% / 1000 h            |  |  |  |  |
| Reliability                                  | FIT<0.017 parts / billions hours         |  |  |  |  |
| Capacitor height                             | 250 µm                                   |  |  |  |  |
| (*) Other values on request (**) w/o packing |  |  |  |  |  |

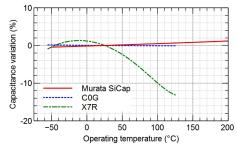


Fig. 1: Capacitance variation vs temperature (for ETSC and MLCC technologies)

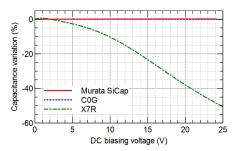


Fig.2: Capacitance variation vs DC biasing voltage @ BV30 (for ETSC and MLCC technologies)

# Capacitance range



Available parts.
For other values, contact your Murata sales representative.

Under development.

Pad finishing in Aluminum. Other finishing available such as nickel or gold.

|      | Case size |      | Pad dimensions (±0.05 μm) |      |      |
|------|-----------|------|---------------------------|------|------|
|      | А         | В    | С                         | d    | е    |
| 0202 | 0.65      | 0.65 | 0.15                      | 0.30 | 0.30 |
| 0404 | 1.07      | 1.07 | 0.15                      | 0.72 | 0.72 |
| 0505 | 1.32      | 1.32 | 0.15                      | 0.97 | 0.97 |
| 0605 | 1.59      | 1.32 | 0.15                      | 1.22 | 1.22 |
| 1208 | 3.07      | 2.07 | 0.15                      | 2.72 | 1.72 |
| 1612 | 4.07      | 3.07 | 0.15                      | 3.72 | 2.72 |
| 1616 | 4.07      | 4.07 | 0.15                      | 3.72 | 3.72 |
| 2016 | 5.07      | 4.07 | 0.15                      | 4.72 | 3.72 |

## **Packaging**

Tape & reel, waffle pack or wafer delivery.





#### Assembly by Soldering

The attachment techniques recommended by Murata for the ETSC capacitors on the customers substrates are fully detailed in specific documents available on our website. To assure the correct use and proper functioning of Murata Silicon capacitors please download the assembly instructions on www.ipdia.com/assembly and read them carefully.



please go to: www.ipdia.com/assembly and download the pdf file called "ETSC / EXSC Capacitors 250 μm - Assembly by Wirebonding"

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